

# Bias Resistor Transistor

## PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

- **Applications**

Inverter, Interface, Driver

- **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on / off conditions need to be set for operation, making the device design easy.

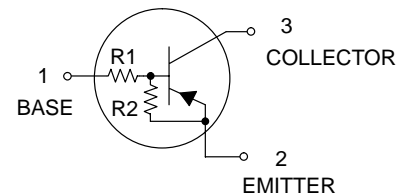
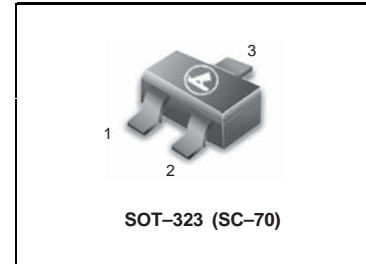
- We declare that the material of product compliance with RoHS requirements.

- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

- **Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V <sub>CC</sub>	-50	V
Input voltage	V <sub>IN</sub>	-12 to +10	V
Output current	I <sub>C</sub>	-500	mA
Power dissipation	P <sub>D</sub>	200	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

**LDTB123EWT1G**  
**S-LDTB123EWT1G**



### DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTB123EWT1G S-LDTB123EWT1G	K5	2.2	2.2	3000/Tape & Reel
LDTB123EWT3G S-LDTB123EWT3G	K5	2.2	2.2	10000/Tape & Reel

- **Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V <sub>I(off)</sub>	-	-	-0.5	V	V <sub>CC</sub> = -5V, I <sub>O</sub> = -100μA
	V <sub>I(on)</sub>	-3	-	-		V <sub>O</sub> = -0.3V, I <sub>O</sub> = -20mA
Output voltage	V <sub>O(on)</sub>	-	-0.1	-0.3	V	I <sub>O</sub> /I <sub>E</sub> = -50mA/-2.5mA
Input current	I <sub>I</sub>	-	-	-3.8	mA	V <sub>I</sub> = -5V
Output current	I <sub>O(off)</sub>	-	-	-0.5	μA	V <sub>CC</sub> = -50V, V <sub>I</sub> =0V
DC current gain	G <sub>I</sub>	39	-	-	-	V <sub>O</sub> = -5V, I <sub>O</sub> = -50mA
Input resistance	R <sub>1</sub>	1.54	2.2	2.86	kΩ	-
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2	-	-
Transition frequency	f <sub>T</sub> *	-	200	-	MHz	V <sub>CE</sub> = -10V, I <sub>E</sub> = 50mA, f= 100MHz

\* Characteristics of built-in transistor

LDTB123EWT1G;S-LDTB123EWT1G

●Electrical characteristic curves

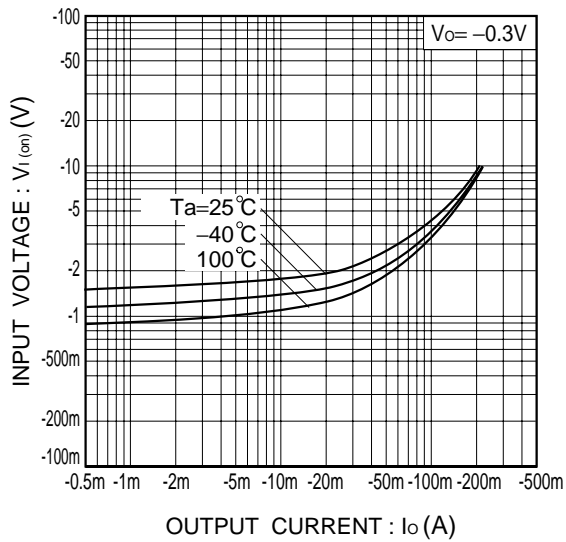


Fig.1 Input voltage vs. output current (ON characteristics)

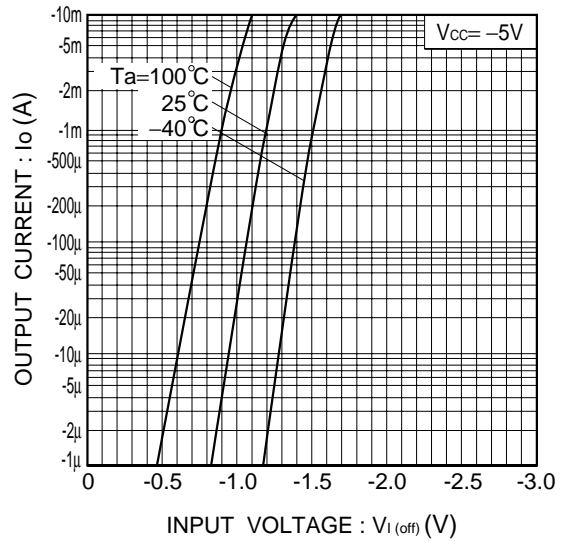


Fig.2 Output current vs. input voltage (OFF characteristics)

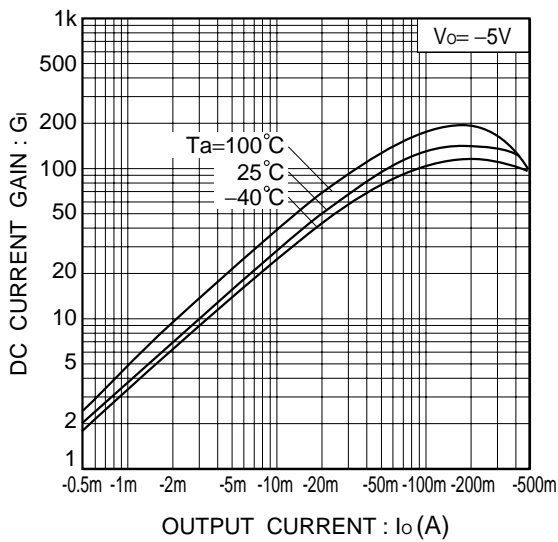


Fig.3 DC current gain vs. output current

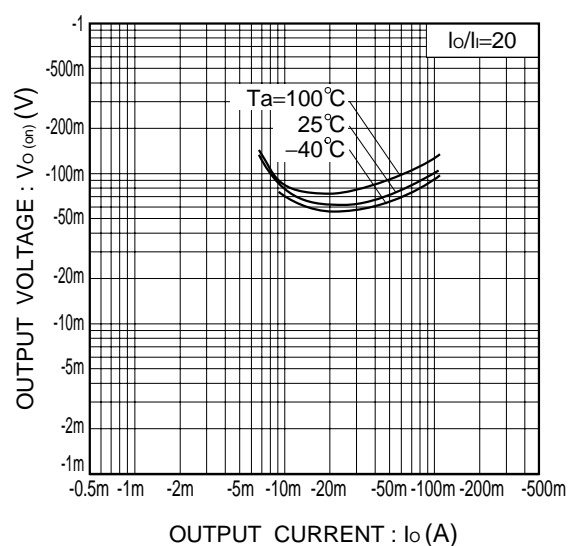
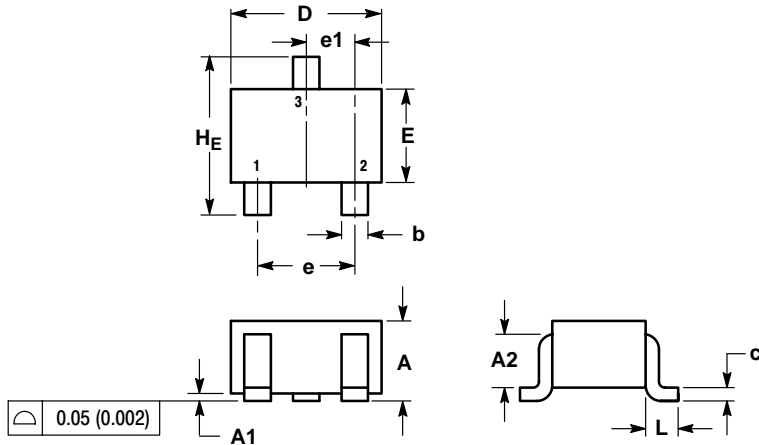


Fig.4 Output voltage vs. output current

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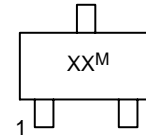
SC-70 (SOT-323)



- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
HE	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT\*

